

	Type	Hits	Search Text	DBs
1	IS&R 6		((("20020179942") or ("20020167082")) or ("20030057479")).PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
2	BRS 709		"257"/\$.ccls.and(LDMOS)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
3	BRS 19		S3 and (capacitive adj coupling)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
4	BRS 80		S3 and (drain adj capacitance)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
5	IS&R 2		("4754310").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Type	Hits	Search Text	DBs
6	IS&R	4	("5216275") or ("5754310")).PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
7	BRS	170375	"257"/\$.ccls.and(LDMOS)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
8	BRS	709	"257"/\$.ccls. and (LDMOS)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
9	BRS	80	S10 and (drain adj capacitance)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
10	BRS	0	S11 and (capacitance adj independent adj of adj voltage)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Type	Hits	Search Text	DBs
11	BRS	21	S13 and independent	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
12	BRS	78	S11 and (capacitance and voltage)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
13	IS&R	2	("5900662").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
14	BRS	87	"257"/\$.ccls. and (LDMOS) and (depletion adj layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
15	BRS	0	"257"/\$.ccls. and (LDMOS) and (drain adj depletion adj capacitance)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Type	Hits	Search Text	DBs
16	BRS	0	"257"/\$.ccls. and (LDMOS) and (drain adj space adj charge adj region)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
17	BRS	2	"257"/\$.ccls. and (LDMOS) and (drain adj depletion adj layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB